Typical geometrical sizes of the Broad Area Diode Laser chip are 1000µm x 500µm x 200µm (length x width x height). The typical emitter width is 100µm. The laser chip is grown by MOVPE of compound semiconductor material. The optical gain is provided by double heterostructure which include several Quantum Wells for electronic confinement. The surfaces of the laser chip act as cavity mirrors due to the difference of the refractive index of the laser material and the surrounding air. The rear facet of the laser chip is provided with an high reflective coating. The front facet of the laser chip is provided with a class A anti-reflection coating for directing the output power to the front facet of the laser chip. The broad area laser chips are mounted as chip on carrier. High power devices are available with up to 0.5W at 740nm and 2W at 980nm. These diode lasers are longitudinal and spatial multimode.
For further information about the product or support requests, please contact your local person in charge.

+ 49 (0)6421 305-0 Germany
+ 1 800 352 3639 United States, Canada

Sacher Lasertechnik GmbH
Rudolf-Breitscheid-Str. 1-5
35037 Marburg
Germany

Sacher Lasertechnik LLC.
5765 Equador Way
Buena Park, CA 90620
United States

Copyright Sacher Lasertechnik Group 2010
http://www.sacher-laser.com
All Rights Reserved.

Sacher Lasertechnik and the Sacher Lasertechnik logo are trademarks or registered trademarks of Sacher Lasertechnik GmbH - Germany, other countries, or both.

The Lasers Systems Lynx™, Tiger™, Cheetah™, Lion™, Cougar™, Jaguar™, Serval™, Serval Plus™ and CAT™ are trademarks or registered trademarks of Sacher Lasertechnik GmbH - Germany, other countries, or both.

Other company, product and service names may be trademarks or service marks of others. References in this publication to Sacher Lasertechnik products or services do not imply that Sacher Lasertechnik intends to make them available in all countries in which Sacher Lasertechnik operates.